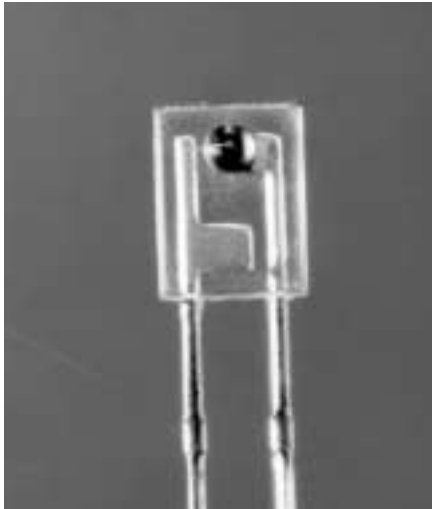


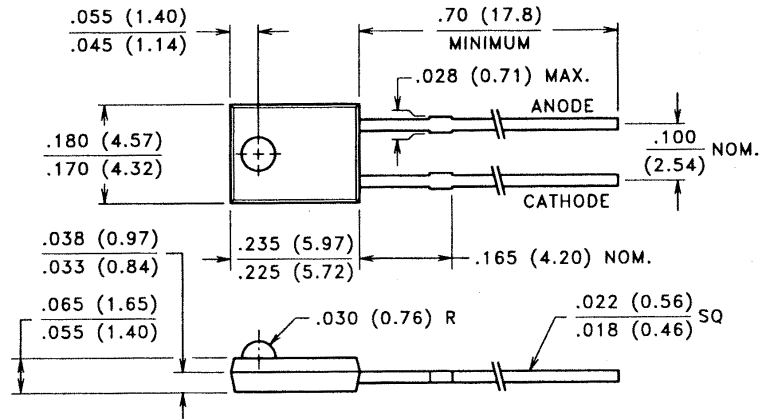
# GaAlAs Infrared Emitting Diodes

Molded Lateral Package — 880 nm

# VTE7172H, 7173H



## PACKAGE DIMENSIONS inch (mm)



CASE 7 LATERAL  
CHIP SIZE: .011" x .011"

## DESCRIPTION

These side-looking packages are designed for use in PC board mounted interrupt detectors. The package is transfer molded plastic and contains a high efficiency, 880 nm, GaAlAs IRED die.

## RoHS Compliant



## ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures									
Storage and Operating:	-40°C to 85°C								
Continuous Power Dissipation:	100 mW								
Derate above 30°C:	1.82 mW/°C								
Maximum Continuous Current:	50 mA								
Derate above 30°C:	0.91 mA/°C								
Peak Forward Current, 10 μs, 100 pps:	2.5 A								
Temp. Coefficient of Power Output (Typ.):	-8%/°C								
Maximum Reverse Voltage:									5.0V
Maximum Reverse Current @ V <sub>R</sub> = 5V:									10 μA
Peak Wavelength (Typical):									880 nm
Junction Capacitance @ 0V, 1 MHz (Typ.):									14 pF
Response Time @ I <sub>F</sub> = 20 mA									
Rise: 1.0 μs									
Fall: 1.0 μs									
Lead Soldering Temperature:									260°C
									(1.6 mm from case, 5 seconds max.)

## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output							Forward Drop		Half Power Beam Angle
	Irradiance				Radiant Intensity	Total Power	Test Current	V <sub>F</sub>		
	E <sub>e</sub>		Condition		I <sub>e</sub>	P <sub>O</sub>	I <sub>FT</sub>	@ I <sub>FT</sub>		θ <sub>1/2</sub>
	mW/cm <sup>2</sup>		distance	Diameter	mW/sr	mW	mA	Volts		Typ.
	Min.	Typ.	mm	mm	Min.	Typ.	(Pulsed)	Typ.	Max.	
VTE7172H	0.4	0.6	16.7	4.6	1.1	2.5	20	1.3	1.8	±25°
VTE7173H	0.6	0.8	16.7	4.6	1.7	5.0	20	1.3	1.8	±25°

■ Refer to General Product Notes, page 2.